

Title (en)

Semiconductor device having programmable read only memory cells for specific mode.

Title (de)

Halbleitergerät mit programmierbaren Nur-Lesespeicherzellen für spezifischen Modus.

Title (fr)

Dispositif semi-conducteur à cellules de mémoire fixe programmables pour mode spécifique.

Publication

EP 0272848 A2 19880629 (EN)

Application

EP 87310864 A 19871210

Priority

JP 30281186 A 19861220

Abstract (en)

A semiconductor device having an internal circuit (5) comprises a program circuit (1) for programming a PROM (2), a discrimination circuit (3) for discriminating the contents of the PROM (2), and a specific mode starting circuit (4) for operating the internal circuit (5) in a specific mode when a specific mode starting signal is output from the discrimination circuit (3). Consequently, the operating mode of semiconductor device can be established and changed by programming and re-programming the PROM (2) without the need for special additional equipment.

IPC 1-7

G11C 17/00; G11C 29/00

IPC 8 full level

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CPC (source: EP KR US)

G06F 15/7814 (2013.01 - EP US); **G11C 16/0441** (2013.01 - EP US); **G11C 16/06** (2013.01 - EP US); **G11C 16/08** (2013.01 - EP US); **G11C 16/10** (2013.01 - EP US); **G11C 16/32** (2013.01 - EP US); **G11C 17/00** (2013.01 - KR); **G11C 17/18** (2013.01 - EP US); **G11C 29/46** (2013.01 - EP US)

Cited by

EP0448958A3; EP1195772A1; EP0617377A3; US5497475A; WO9418676A3

Designated contracting state (EPC)

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DOCDB simple family (publication)

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